

Data sheet acquired from Harris Semiconductor SCHS052

CMOS Analog Multiplexers/Demultiplexers

High-Voltage Types (20-Volt Rating)

CD4067B - Single 16-Channel

Multiplexer/Demultiplexer CD4097B — Differential 8-Channel Multiplexer/Demultiplexer

■ CD4067B and CD4097B CMOS

analog multiplexers/demultiplexers* are digitally controlled analog switches having low ON impedance, low OFF leakage current, and internal address decoding. In addition, the ON resistance is relatively constant over the full input-signal range.

The CD4067B is a 16-channel multiplexer with four binary control inputs, A,B,C,D, and an inhibit input, arranged so that any combination of the inputs selects one switch.

The CD4097B is a differential 8-channel multiplexer having three binary control inputs A, B, C, and an inhibit input. The inputs permit selection of one of eight pairs of switches.

A logic "1" present at the inhibit input turns all channels off.

The CD4067 and CD4097 are supplied in 24-lead dual-in-line welded-seal ceramic packages (D suffix), 24-lead dual-in-line frit-seal ceramic packages (F suffix), 24-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Recommended Operating Conditions at TA = 25°C (Unless Otherwise Specified)

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges. Values shown apply to all types except as

notea.			
Characteristic	Min.	Max.	Units
Supply-Voltage Range (T _A =Full Package- Temp. Range)	3	18	٧
Multiplexer Switch Input Current Capability	1 -	25	mΑ
Output Load Resistance	100	-	·Ω.

NOTE:

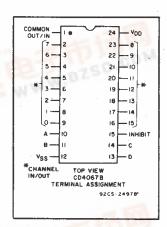
In certain applications, the external load-resistor current may include both VpD and signal-line components. To avoid drawing VpD current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from RQN values shown in ELECTRICAL CHARACTERISTICS CHART). No VpD current will flow through RL if the switch current flows into terminal 1 on the CD4067; terminals 1 and 17 on the CD4097.

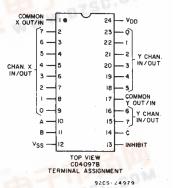
Features:

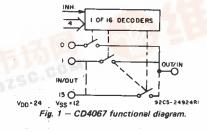
- Low ON resistance: 125 Ω (typ.) over 15
 V_{p-p} signal-input range for V_{DD}-V_{SS}=15 V
- High OFF resistance: channel leakage of ±10 pA (typ.) @ VDD-VSS=10 V
- Matched switch characteristics: R_{ON}=5 Ω (typ.) for V_{DD}-V_{SS}=15 V
- Very low quiescent power dissipation under all digital-control input and supply conditions: 0.2 μW (typ.) @ VDD-VSS=10 V
- Binary address decoding on chip
- 5-V, 10-V, and 15-V parametric ratings
- 100% tested for quiescent current at 20 V
- Standardized symmetrical output characteristics
- Maximum input current of 1 μA at 18 V over full package temperature range;
 100 nA at 18 V and 25°C
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Analog and digital multiplexing and demultiplexing
- A/D and D/A conversion
- Signal gating







CD4067 TRUTH TABLE

	CDW	007	OF INUINIABLE					
A	В	С	D	Inh	Selected Channel			
Х	Х	Х	х	1	None			
0	0	0	0	0	0			
1	0	0	0	.0.	1 .			
0	1	0	0.	0	2			
1	1	0	0	0	3			
0	0	1	0	0	4			
1	0	1	0	0	5			
0	1	1	0	0	6			
1	1	1	0	0	.7			
0	0	0	1	0	8			
1	0	0	1	0	9			
0	1	0	1	0	10			
1	1	0	1	0	11			
0	0	1	1	0	12			
1	0	1	1	0	13			
0	1	1	1	0	14			
1	1	1	1	0	15			

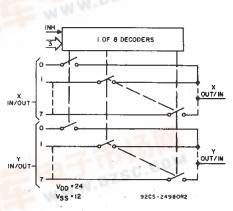


Fig. 2-CD4097 functional diagram.

CD4097 TRUTH TABLE

A	В	С	Inh	Selected Channel
Х	Х	Х	1	None
0	0	0	.0	0X, 0Y
1	0	0	0	1X, 1Y
0	1	0	0	2X, 2Y
1	1	0	0	3X, 3Y
0	0	1	0	4X, 4Y
1	0	1	0	5X, 5Y
0	1	1	0	6X, 6Y
1	1	1	0	7X, 7Y

When these devices are used as demultiplexers, the channel in/out terminals are the outputs and the common out/in terminals are the inputs.

ELECTRICAL CHARACTERISTICS

CHARAC- TERISTIC	(CONDITIONS	ONDITIONS LIMITS AT INDICATED TE				ED TEI	MPER/	ATURES	(°C)	Units
	Vis	٧ _{SS}	V _{DD}	-55	-40	+85	+125		+25		1
	(V)	(V)	(V)				L	Min.	Тур.	Max.	1
SIGNAL INF	UTS (V _{is}) AND OUT	PUTS (
Quiescent			5	5	5	150	150		0.04	5	
Device Cur-			10	10	10	300	.300	_	0.04	10	μΑ
rent, IDD Max.			15 20	20 100	100	600 3000	600		0.04	20	
ON-state Re			20	100	100	3000	3000		0.08	100	
sistance			_	000	050						ļ
V _{SS} ≤ V∷≤Voo		0	5	800	850	1200	1300		470	1050	
V _{is} ≤V _{DD} r _{on} Max.		0	10	310	330	520	550		180	400	÷ Ω
Change in		0	15_	200	210	300	320		125	240	- *
on-state Resistance							,				
(Between							1.5] .		
Any Two		0	5	L - 1	_	-	'-		15	-	
Channels)		0	10			-		- ,	. 10		Ω
Δr _{on}		0	15	-					5	· · _ ·	
OFF Chan- nel Leak- age Cur- rent: Any Channel				*	ţ						
OFF Max. or All Chan- nels OFF (Common		0	18	±1	00*	±100	0*	_	±0.1	±100*	nA
OUT/IN) Max Capacitance:											
Input, C _{is}				_	-	-	_	_	5	_	:
Cos CD4067				_	_	_	_		55	_	
CD4097		-5	5				-		35		рF
Feed- through,				-	_	-			0.2		
C _{ios}											ļ
Propaga- tion Delay	, ,	R _L = 200 KΩ	5		_	_	-	_	30	60	
Time (Sig-	VDD	C _L =50 pF	10				_		15	30	ns
nal Input	7	t _r ,t _f =20 ns	15	_	_	_	_	_	10	20	
to Output	/ADDG	RESS or INHIB	71.17				1,4	L.,	ــــــــــــــــــــــــــــــــــــــ		L
	ומטאי	$R_1 = 1 \text{ K}\Omega$		<u> </u>			·		1		
Input Low	1	to VSS	- 5		1.5	· .	-		, ;—,;	1.5	1
Voltage,	=V _{DD}	I _{4S} <2 μA	10	ļ	3				<u> </u>	3	1
V _{IL} Max.	thru	on all OFF	15	<u> </u>	4					4	V
Input High	$1_{K\Omega}$	Channels	5		3.5			3.5	<u> </u>	-] *
Voltage,			10		7			7	-	_	1
V _{IH} Min.			15		11	-		11		-	1
										K	

^{*} Determined by minimum feasible leakage measurement for automatic testing.

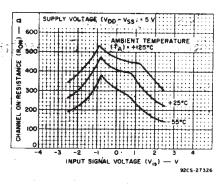


Fig. 3—Typical ON resistance vs. input signal voltage (all types).

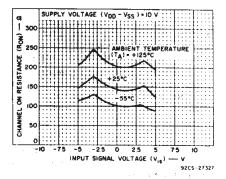


Fig. 4—Typical ON resistance vs. input signal voltage (all types).

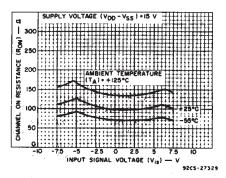


Fig. 5—Typical ON resistance vs. input signal voltage (all types).

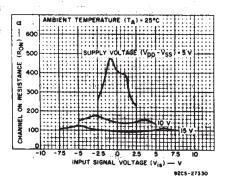


Fig. 6—Typical ON resistance vs. input signal voltage (all types).

ELECTRICAL CHARACTERISTICS (Cont'd)

CHARAC- TERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)					Units		
	Vis	VSS	V _{DD}	-55	-40	+85	+125		+25		
	(V)	(V)	(V)					Min.	Тур.	Max.	
Input Current, I _{IN} Max.	V _{IN} =	0, 18 V	18	±0.1	±0.1	±1	±1	, -	±10 ⁻⁵	±0.1	μΑ
Propagation Delay Time: Address or		KΩ,CL= c _r ,t _f =20 ns									
Inhibit-to-		0	5	_				_	325	650	
Signal OUT (Channel		0	10		~	_	-	_	135	270	ns
turning ON)		0	15	-	_	_			95	190	1
Address or Inhibit-to-) Ω,C _L = t _r ,t _f =20 ns									<u> </u>
Signal OUT		0	5	1 –	_	→ .	-		220	440	
(Channel turning		0	10	_	_			_	90	180	ns
OFF)		0	15			1	-	_	65	130	1
Input Capaci- tance, C _{IN}	Any Address or Inhibit Input					_	_	-	5	7.5	pF

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V _{DD})	
Voltages referenced to V _{SS} Terminal)	
INPUT VOLTAGE RANGE, ALL INPUTS	0.5V to V _{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -55°C to +100°C	500mW
For T _A = +100°C to +125°C	
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	·
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Ty	pes) 100mW
OPERATING-TEMPERATURE RANGE (TA)	
STORAGE TEMPERATURE RANGE (Tstg)	65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79mm) from case for 10s max	+265°C

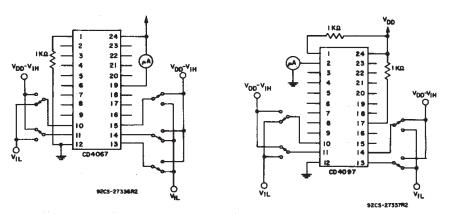
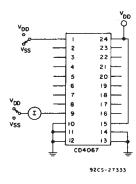


Fig. 8—Input voltage—measure \leq 2 μ A on all OFF channels (e.g., channel 12).

TEST CIRCUITS



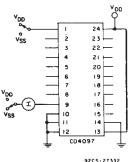
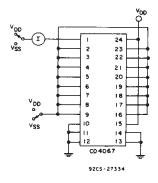


Fig. 7-OFF channel leakage current-any channel OFF.



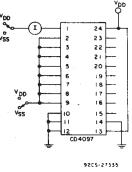
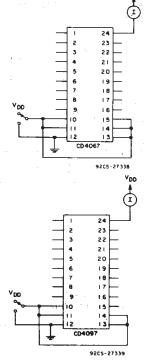


Fig. 9-OFF channel leakage current-all channels OFF.

ELECTRICAL CHARACTERISTICS (Cont'd)

			TE	ST COND	ITIONS			3 T T T
CHARAC- TERISTIC	V _{is} (V)	V _{DD} (V)	R _L (KΩ)		-	in en en	TYPICAL VALUES	UNITS
Cutoff	5 •	10	1					
(-3-dB) Frequency		.,		V at Co	mmon OUT/IN	CD4067	14	
Channel ON	20 loc	V _{OS} =;	3 dB			CD4097	20	MHz
(Sine Wave Input)	$20 \log \frac{V_{os}}{V_{is}} = -3 dB$		V _{OS} at Any Channel			60	1411.17	
Total	2.	5			-		0.3	
Harmonic Distortion,	3.	10	10				0.2	_
THD	5 [•]	15					0.12	%
		k'Hz sine	wave					
-40-dB	5 °	10	1					
Feedthrough Frequency	V _{OS} 40 4B			V _{os} at Common OUT/IN CD4097 V _{os} at Any Channel			20	
(All Channels	70 100 =40 0 K		12				MHz	
OFF	Vis							
	5 [®]	10	1					
Signal Cross-				Between /	Any 2 Channels		1	
talk (Fre- quency at	20 100	Vos	10 dB	Between Sections	Measured on Co	ommon	10	MHz
-40 dB)	20 log	Vis	70 db	CD4097 Measured on Al Only Channel		ny	18	IVITIZ
	-	10	10*					
Address-or- Inhibit-to- Signal Crosstalk	VC=A	DD ^{-V} S re Wave)	S	,			75	mV (Peak)

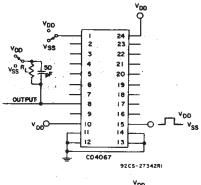


TEST CIRCUITS (Cont'd)

Fig. 10- Quiescent device current.

Peak-to-peak voltage symmetrical about $\frac{V_{DD}-V_{SS}}{2}$

- Worst case.
- * Both ends of channel.



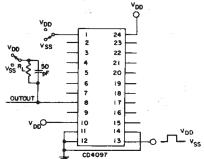
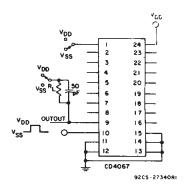


Fig. 12— Turn-on and turn-off propagation delay inhibit input to signal output (e.g. measured on channel 1).



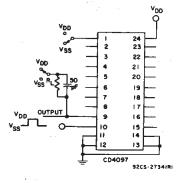
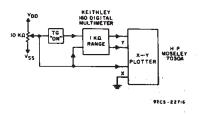
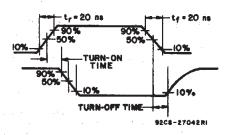


Fig. 11 – Turn-on and turn-off propagation delay—address select input to signal output (e.g. measured on channel 0).





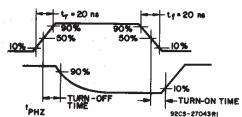


Fig. 13- Channel ON resistance measurement circuit.

Fig. 14- Propagation de/ay waveform channel being turned ON (R $_{L}$ = 10 K $\Omega_{\rm r}$ C $_{L}$ = 50 pF).

Fig. 15- Propagation delay waveform, channel being turned OFF (R $_{L}$ = 300 Ω_{z} $C_L = 50 \ pF$).

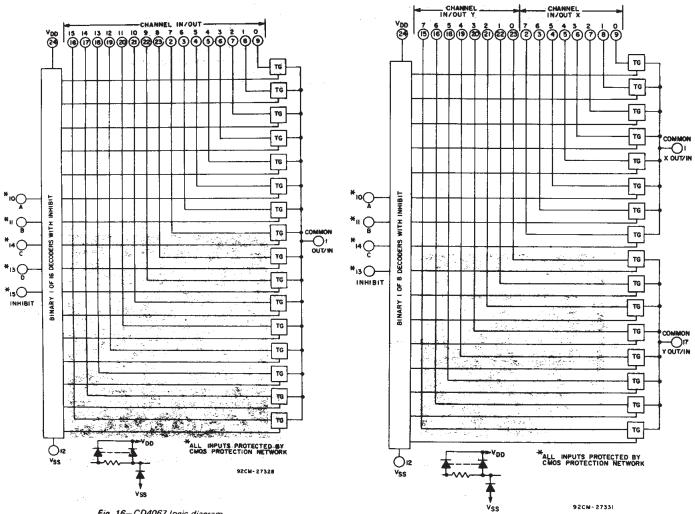


Fig. 16-CD4067 logic diagram.

Fig. 17-CD4097 logic diagram.

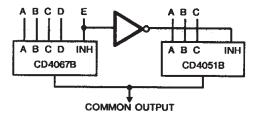


Fig. 18-24-to-1 MUX Addressing

SPECIAL CONSIDERATIONS

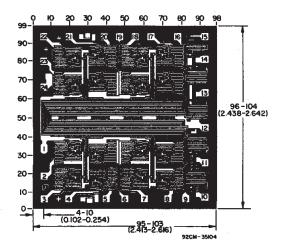
In applications where separate power sources are used to drive V_{DD} and the signal inputs, the V_{DD} current capability should exceed V_{DD}/R_L (R_L =effective external load). This provision avoids permanent current flow or clamp action on the V_{DD} supply when power is applied or removed from the CD4067B or CD4097B.

When switching from one address to another, some of the ON periods of the channels of the multiplexers will overlap momentarily, which may be objectionable in certain applications. Also when a channel is turned on or off by an address input, there is a momentary conductive path from the channel to VSS, which will dump some charge from any capacitor connected to the input or output of the channel. The inhibit input turning on a channel will similarly dump some charge to VSS.

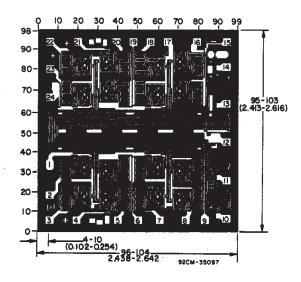
The amount of charge dumped is mostly a function of the signal level above VSS. Typically, at V_{DD} -VSS=10 V, a 100-pF

capacitor connected to the input or output of the channel will lose 3-4% of its voltage at the moment the channel turns on or off. This loss of voltage is essentially independent of the address or inhibit signal transition time, if the transition time is less than 1-2 µs. When the inhibit signal turns a channel off, there is no charge dumping to VSS. Rather, there is a slight rise in the channel voltage level (65 mV typ.) due to capacitive coupling from inhibit input to channel input or output. Address inputs also couple some voltage steps onto the channel signal levels.

In certain applications, the external load-resistor current may include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from R_{ON} values shown in ELECTRICAL CHARACTERISTICS CHART). No V_{DD} current will flow through R_L if the switch current flows into terminal 1 on the CD4067B, terminals 1 and 17 on the CD4097B.



Dimensions and pad layout for CD4067BH.



Dimensions and pad layout for CD4097BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils $(10^{-3} \, \text{inch})$.

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